

## ECE 2EI4 Quiz 3 (Section 1)

Use the following formulae in your solutions

### NMOS Transistor Mathematical Model

Cut off region  $i_{DS}=0$  for  $v_{GS} < V_{TN}$

Linear region  $i_{DS} = K_n (v_{GS} - V_{TN} - 0.5 v_{DS}) v_{DS}$  for  $v_{GS} - V_{TN} \geq v_{DS} \geq 0$

Saturation region  $i_{DS} = \frac{K_n}{2} (v_{GS} - V_{TN})^2 (1 + \lambda v_{DS})$  for  $v_{DS} \geq v_{GS} - V_{TN} \geq 0$

### PMOS Transistor Mathematical Model

Cut off region  $i_{SD}=0$  for  $v_{SG} < -V_{TP}$

Linear region  $i_{SD} = K_p (v_{SG} + V_{TP} - 0.5 v_{SD}) v_{SD}$  for  $v_{SG} + V_{TP} \geq v_{SD} \geq 0$

Saturation region  $i_{SD} = \frac{K_p}{2} (v_{SG} + V_{TP})^2 (1 + \lambda v_{SD})$  for  $v_{SD} \geq v_{SG} + V_{TP} \geq 0$

### Small signal Model Parameter of NMOS Transistors

$$g_m = \sqrt{2 K_n I_{DS} (1 + \lambda V_{DS})}$$

$$r_o = \frac{\frac{1}{\lambda} + V_{DS}}{I_{DS}}$$

### Propagation delays for reference CMOS inverter with $V_{DD}=5V$ , $V_{TN}=1V$ and $V_{TP}=-1V$

$$\tau_{PHL} = 0.322 \frac{C}{K_n}$$

$$\tau_{PLH} = 0.322 \frac{C}{K_p}$$

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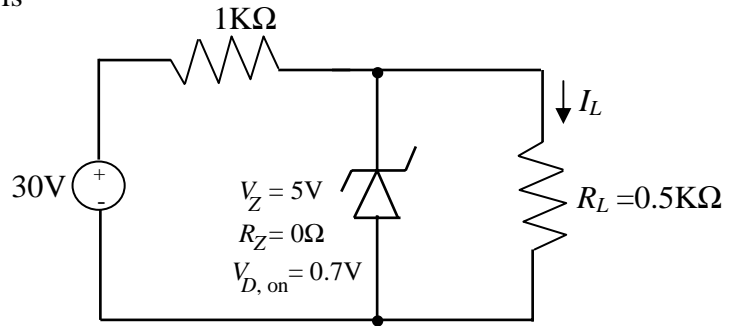
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1) For the shown circuit, the load current  $I_L$  is

- a) -10 mA
- b) 1.4 mA
- c) 20 mA
- d) 10 mA
- e) -1.4 mA

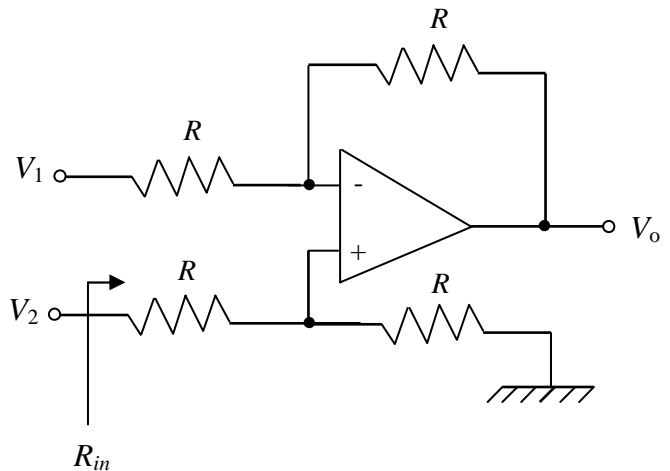


2) In question (1), the smallest allowed value of the load resistance  $R_L$  for the Zener diode to work as a regulator is

- a) 0.1 KΩ
- b) 0.2 KΩ
- c) 0.3 KΩ
- d) 0.4 KΩ
- e) 0.5 KΩ

3) The input resistance  $R_{in}$  for the shown ideal OpAmp circuit is

- a)  $\infty \Omega$
- b)  $0 \Omega$
- c)  $0.5R \Omega$
- d)  $R \Omega$
- e)  $2R \Omega$

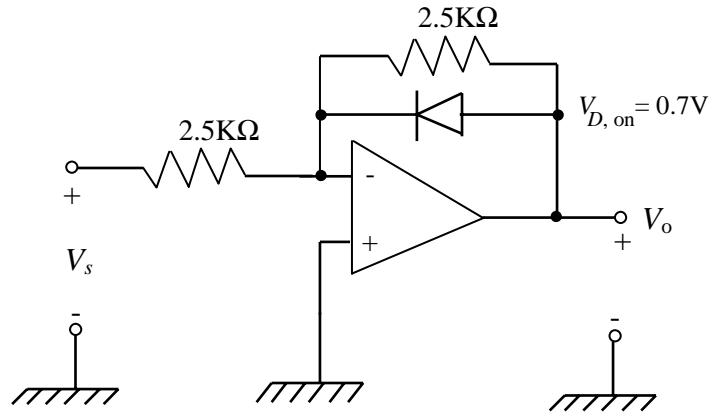


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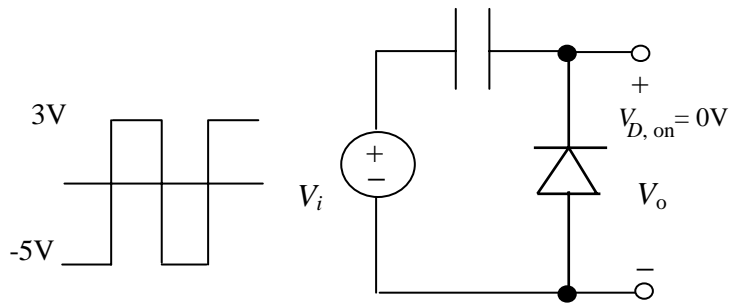
4) For the shown circuit, if  $V_s = -2.0$  V then  $V_o$  is

- a) -2.0 V
- b) -0.7 V
- c) 0.7 V
- d) 2.0 V
- e) -4.0 V



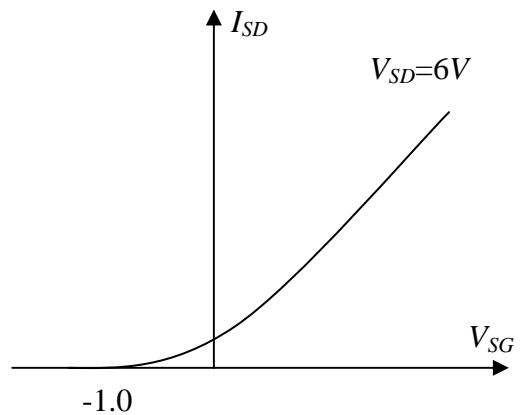
5) The maximum and minimum values of the output voltage  $V_o$  for the shown periodic input signal are

- a) 8.0 V, 0 V
- b) 0 V, -8.0 V
- c) 3.0 V, -3.0 V
- d) 5.0 V, -5.0 V
- e) 3.0 V, 0 V



6) The shown transfer characteristics is for

- a) depletion type NMOS
- b) depletion type PMOS
- c) enhancement type NMOS
- d) enhancement type PMOS
- e) enhancement type CMOS

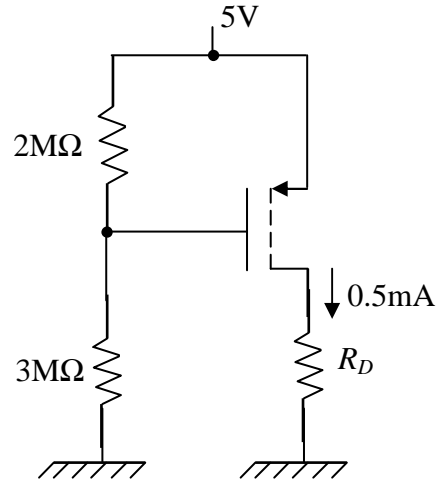


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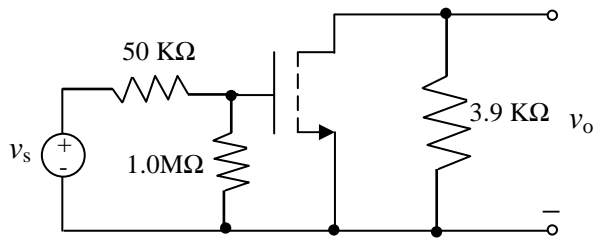
7) The shown enhancement PMOS transistor is operating in the saturation region with  $I_{SD}=0.5\text{ mA}$ . Given that  $V_{TP}=-1.0\text{ V}$ ,  $K_p=1.0\text{ mA/V}^2$  and  $\lambda=0\text{ V}^{-1}$ , the largest value of the resistance  $R_D$  to maintain saturation operation is

- a) 1.0 K $\Omega$
- b) 2.0 K $\Omega$
- c) 4.0 K $\Omega$
- d) 6.0 K $\Omega$
- e) 8.0 K $\Omega$



8) The figure to the right shows the ac equivalent circuit of an amplifier circuit with  $K_n=1.0\text{ mA/V}^2$ ,  $V_{TN}=1.0\text{ V}$  and  $\lambda=0\text{ V}^{-1}$ . Given that the operating point is  $(I_{DS}, V_{DS})=(2.0\text{ mA}, 7.5\text{ V})$ , the small signal gain  $v_o/v_s$  is approximately

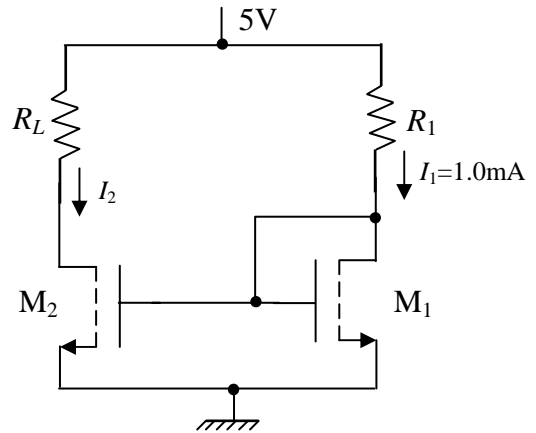
- a) -3.2
- b) 3.2
- c) -7.4
- d) 7.4
- e) -5.3



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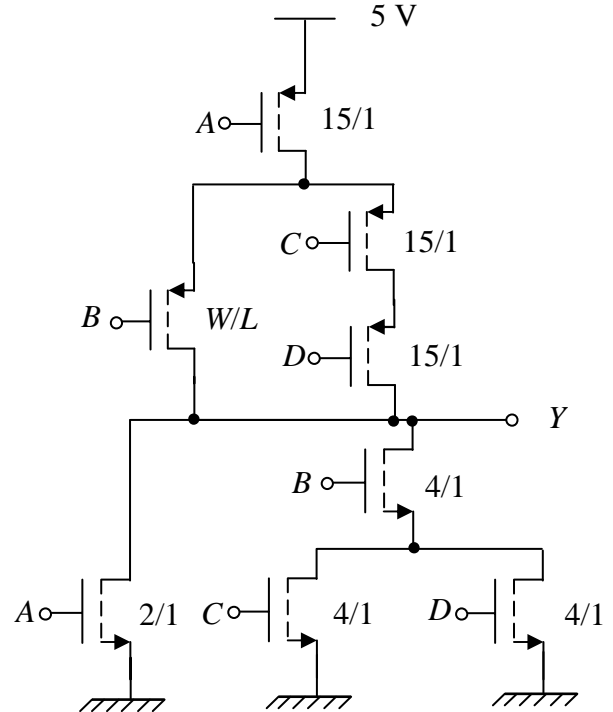
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9) Consider the circuit shown to the right. The bias resistor  $R_1$  and the load resistor  $R_L$  are selected such that both transistors  $M_1$  and  $M_2$  operate in the saturation region. Given that  $V_{TN1} = V_{TN2} = 1.0 \text{ V}$ ,  $K'_{N1} = K'_{N2} = 1.0 \text{ mA/V}^2$ ,  $(W/L)_1 = 2/1$  and  $(W/L)_2 = 6/1$ , and  $\lambda_1 = \lambda_2 = 0 \text{ V}^{-1}$ , the current  $I_2$  is



- a) 3.0 mA
- b) 2.0 mA
- c) 1.0 mA
- d) 0.33 mA
- e) None of the above

10) The shown CMOS circuit implements the logic function  $Y = \overline{A + BC + BD}$ . To obtain worst case delay equal to that of a reference CMOS inverter, the ratio  $W/L$  should be



- a) 15/1
- b) 5/1
- c) 2.5/1
- d) 7.5/1
- e) 2/1